

Silicon Tuning Diode

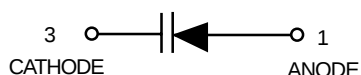
This device is designed in the Surface Mount package for general frequency control and tuning applications. It provides solid-state reliability in replacement of mechanical tuning methods.

- High Q with Guaranteed Minimum Values at VHF Frequencies
- Controlled and Uniform Tuning Ratio

MMBV3102LT1



CASE 318-08, STYLE 8
SOT- 23 (TO-236AB)



MAXIMUM RATINGS(EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	Vdc
Forward Current	I_F	200	mAdc
Device Dissipation @ $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Junction Temperature	T_J	+125	$^\circ\text{C}$
Storage Temperature Range	T_{slg}	-55 to +150	$^\circ\text{C}$

DEVICE MARKING

MMBV3102LT1= M4C

ELECTRICAL CHARACTERISTICS($T_A=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R=10\mu\text{Adc}$)	$V_{(BR)R}$	30	—	—	Vdc
Reverse Voltage Leakage Current ($V_R=15\text{Vdc}$)	I_R	—	—	0.1	μAdc
Diode Capacitance Temperature Coefficient ($V_R=4.0\text{Vdc}$, $f=1.0\text{MHz}$)	T_{CC}	—	300	—	ppm/ $^\circ\text{C}$

Device Type	C_T Diode Capacitance $V_R=3.0\text{Vdc}$, $f=1.0\text{MHz}$ pF			Q, Figure of Merit $V_R=3.0\text{Vdc}$ $f=50\text{MHz}$	C_R , Capacitance Ratio C_3/C_{25} $f=1.0\text{MHz}$	
	Min	Nom	Max	Min	Min	Typ
MMBV3102LT1	20	22	25	200	4.5	4.8

TYPICAL CHARACTERISTICS

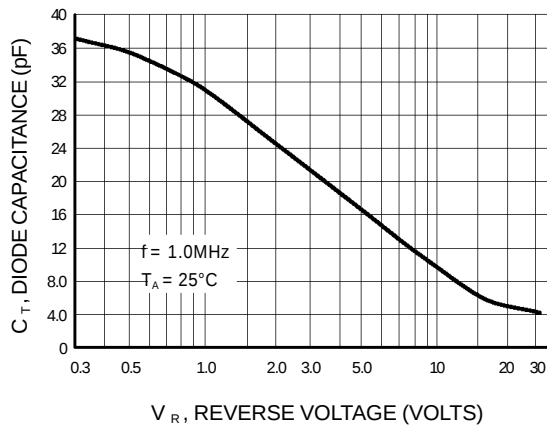


Figure 1. Diode Capacitance

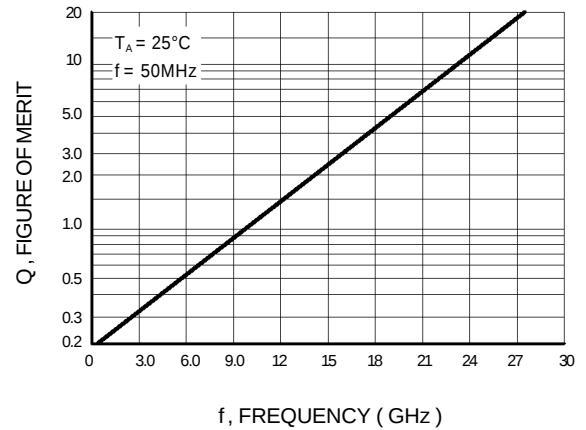


Figure 2. Figure of Merit

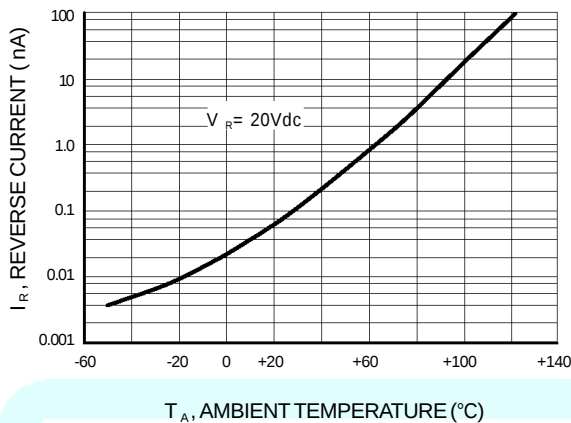


Figure 3. Leakage Current

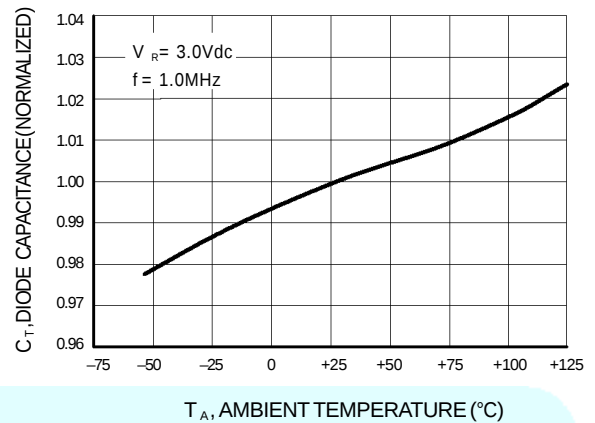


Figure 4. Diode Capacitance

NOTES ON TESTING AND SPECIFICATIONS

1. C_R is the ratio of C_T measured at 3.0 Vdc divided by C_T measured at 25 Vdc.